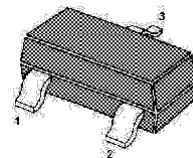
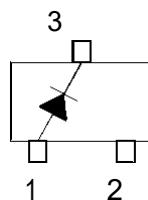


1SS294 SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

- Small surface mounting type
- Low reverse current
- Low forward voltage



Marking Code: "XM"
SOT-23 Plastic Package

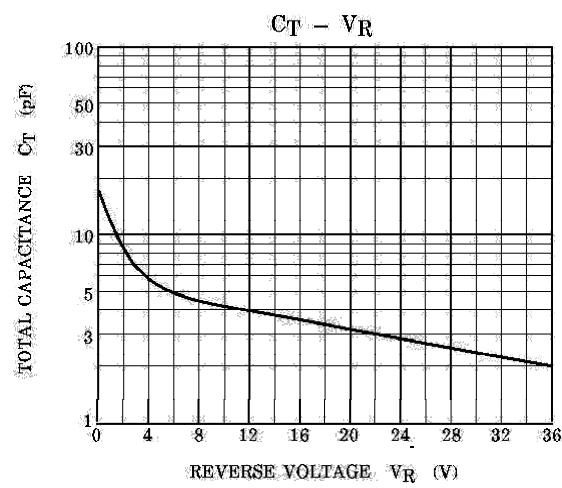
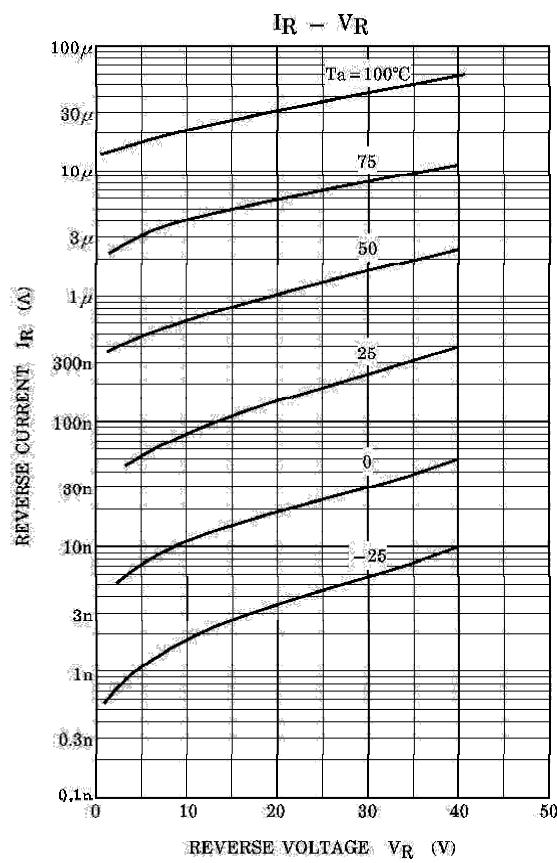
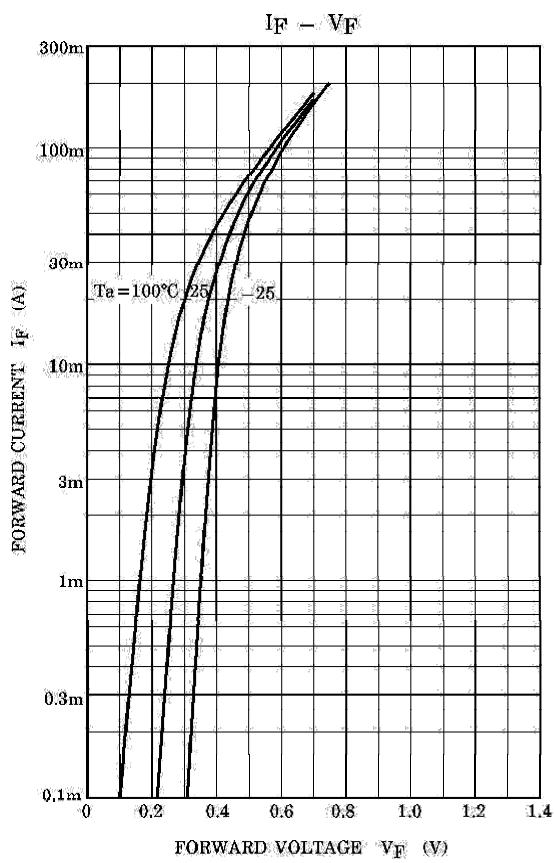
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Average Forward Current	I_O	100	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Power Dissipation	P_D	150	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100 \text{ mA}$	V_F	0.6	V
Reverse Current at $V_R = 40 \text{ V}$	I_R	5	μA
Total Capacitance at $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_T	25	pF

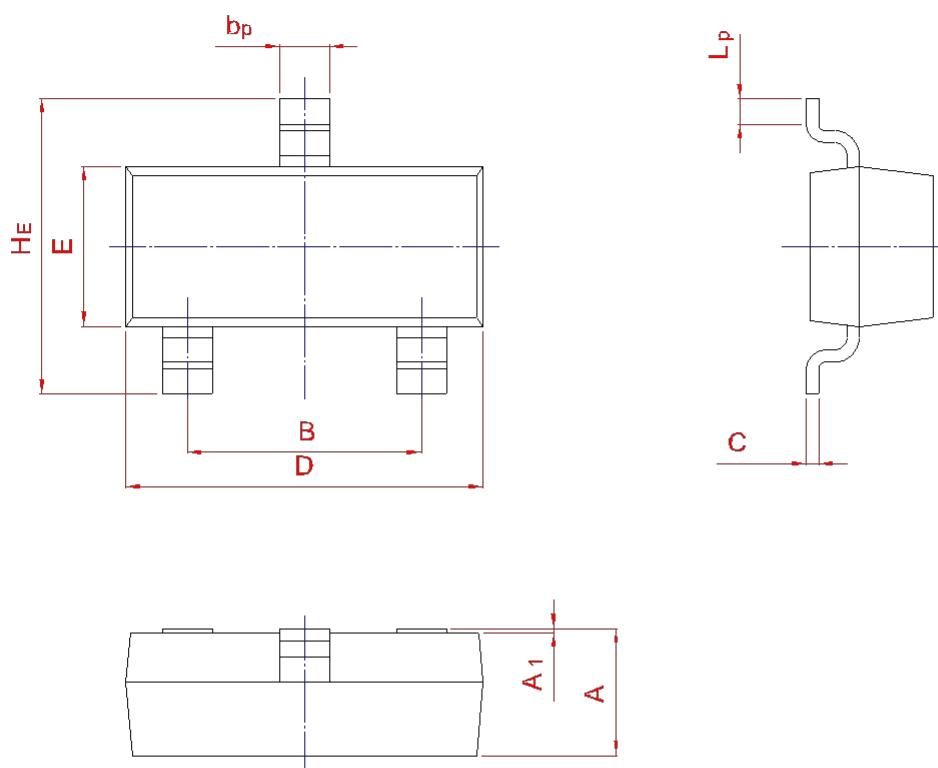
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b _P	C	D	E	H _E	A ₁	L _P
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20